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	Electrical Rating	Symb	ool Min	Ту	o Max	Unit	Sales Contacts RFQ/Samples		
	Collector to Emitter Saturation Voltage	V _{CE(s}	sat)		1.00	\vee			
	Meximum Florida Define	Maximum Electrical Rating Symbol Min Typ Max Unit							
	Maximum Electrical Rating Breakdown Voltage, Collector-Base (Emitter Oper	1)	V _{BR(CBO)}	WIN	Typ Max 80.00				
	Collector Current (dc)	·/	I _C		15.00	A			
	Collector-Emitter Voltage (Base Open)		V _{CEO} 80.00 V V _{EBO} 6.00 V						
	Emitter-Base Voltage (Collector Open)								
	Power Dissipation, Total		P _T		160.00) VV	W		
	 This part can be found in the following product categories: Discretes > Transistors > BJT(BiPolar Junction Transistor) > PNP Transistor Non-Radiation Hardened Devices > Transistors > BJT(BiPolar Junction Transistor) > NPN Transistor 								

